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**(54) METHOD FOR
ETCHING WORK AND
APPARATUS THEREFOR****(57) Abstract:**

PROBLEM TO BE SOLVED: To improve the efficiency of an etching stage by continuously supplying gaseous XeF₂ and executing etching while the etching is heretofore executed by pulsatively supplying gaseous XeF₂.

SOLUTION: An XeF₂ supplying section 12 consists of an XeF₂ source chamber 16 including a tray and ampoule 17 for an XeF₂ crystal 17a, a tank 18 via a valve 19, a flow rate controller 13 supplied with this material by the tank 18 and a valve 20 between the tank 18 and the flow rate controller 13. Pressure sources 21, 22 are provided respectively to maintain the tank 18 and the XeF₂ source chamber 16 at the sublimation pressure of the XeF₂. This apparatus ensures the stable supply of the XeF₂ to an etching chamber.

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